Lattice Semiconductor Corporation - LCMXO2-4000HE-4TG144C Datasheet

Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

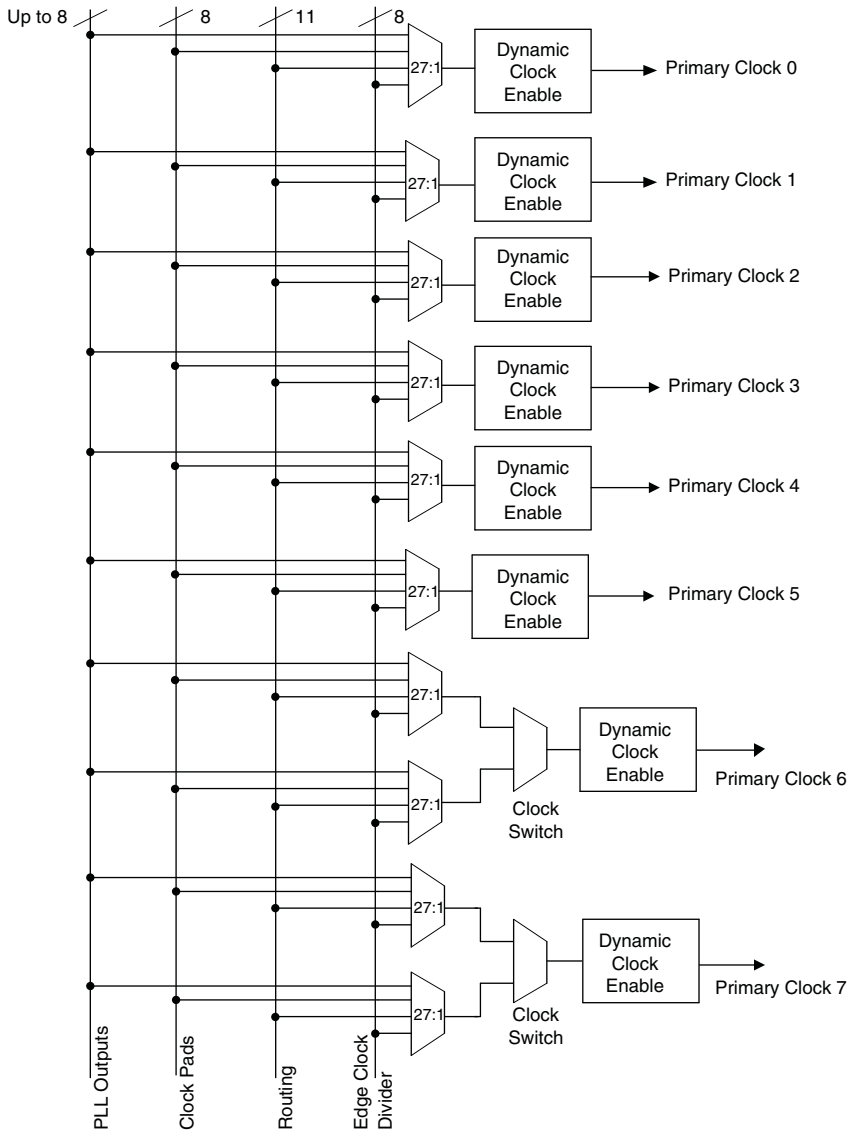
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	540
Number of Logic Elements/Cells	4320
Total RAM Bits	94208
Number of I/O	114
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-4000he-4tg144c

Figure 2-5. Primary Clocks for MachXO2 Devices

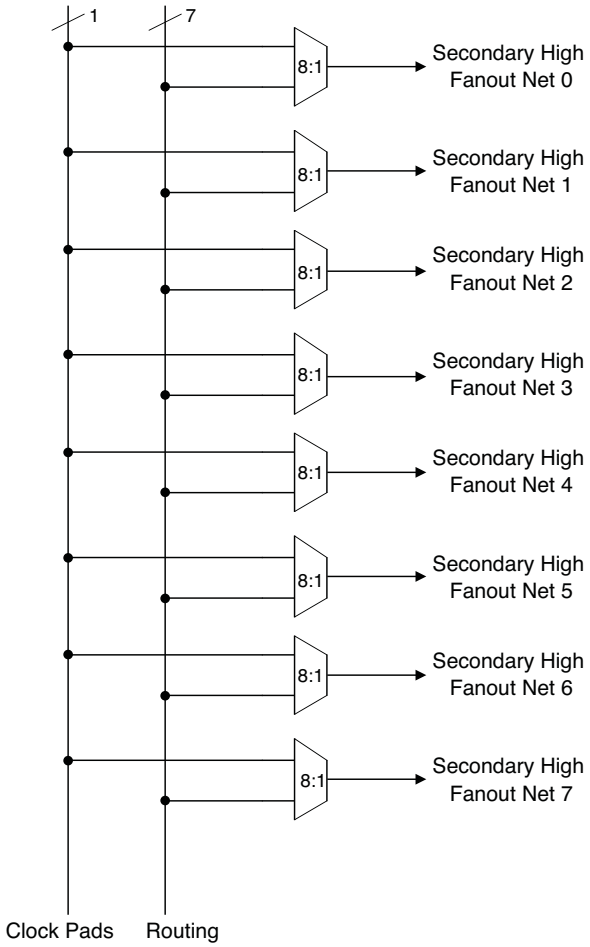


Primary clocks for MachXO2-640U, MachXO2-1200/U and larger devices.

Note: MachXO2-640 and smaller devices do not have inputs from the Edge Clock Divider or PLL and fewer routing inputs. These devices have 17:1 muxes instead of 27:1 muxes.

Eight secondary high fanout nets are generated from eight 8:1 muxes as shown in Figure 2-6. One of the eight inputs to the secondary high fanout net input mux comes from dual function clock pins and the remaining seven come from internal routing. The maximum frequency for the secondary clock network is shown in MachXO2 External Switching Characteristics table.

Figure 2-6. Secondary High Fanout Nets for MachXO2 Devices



sysCLOCK Phase Locked Loops (PLLs)

The sysCLOCK PLLs provide the ability to synthesize clock frequencies. The MachXO2-640U, MachXO2-1200/U and larger devices have one or more sysCLOCK PLL. CLKI is the reference frequency input to the PLL and its source can come from an external I/O pin or from internal routing. CLKFB is the feedback signal to the PLL which can come from internal routing or an external I/O pin. The feedback divider is used to multiply the reference frequency and thus synthesize a higher frequency clock output.

The MachXO2 sysCLOCK PLLs support high resolution (16-bit) fractional-N synthesis. Fractional-N frequency synthesis allows the user to generate an output clock which is a non-integer multiple of the input frequency. For more information about using the PLL with Fractional-N synthesis, please see TN1199, MachXO2 sysCLOCK PLL Design and Usage Guide.

Each output has its own output divider, thus allowing the PLL to generate different frequencies for each output. The output dividers can have a value from 1 to 128. The output dividers may also be cascaded together to generate low frequency clocks. The CLKOP, CLKOS, CLKOS2, and CLKOS3 outputs can all be used to drive the MachXO2 clock distribution network directly or general purpose routing resources can be used.

The LOCK signal is asserted when the PLL determines it has achieved lock and de-asserted if a loss of lock is detected. A block diagram of the PLL is shown in Figure 2-7.

The setup and hold times of the device can be improved by programming a phase shift into the CLKOS, CLKOS2, and CLKOS3 output clocks which will advance or delay the output clock with reference to the CLKOP output clock.

Figure 2-8. sysMEM Memory Primitives

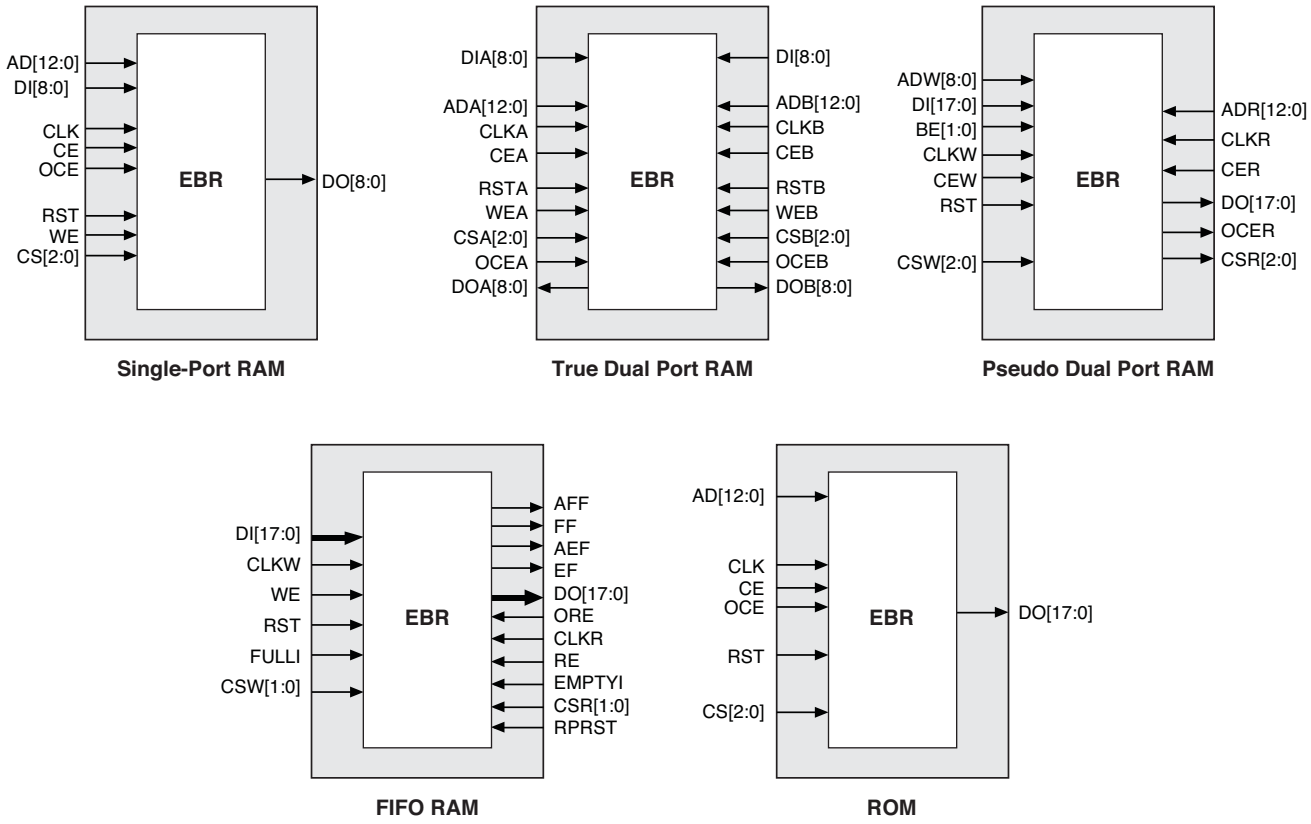
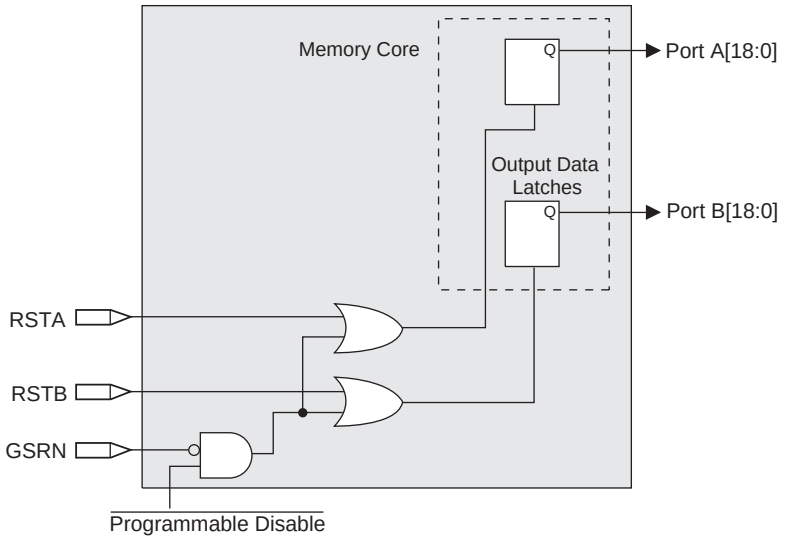


Table 2-6. EBR Signal Descriptions

Port Name	Description	Active State
CLK	Clock	Rising Clock Edge
CE	Clock Enable	Active High
OCE[1]	Output Clock Enable	Active High
RST	Reset	Active High
BE[1]	Byte Enable	Active High
WE	Write Enable	Active High
AD	Address Bus	—
DI	Data In	—
DO	Data Out	—
CS	Chip Select	Active High
AFF	FIFO RAM Almost Full Flag	—
FF	FIFO RAM Full Flag	—
AEF	FIFO RAM Almost Empty Flag	—
EF	FIFO RAM Empty Flag	—
RPRST	FIFO RAM Read Pointer Reset	—

1. Optional signals.
2. For dual port EBR primitives a trailing ‘A’ or ‘B’ in the signal name specifies the EBR port A or port B respectively.
3. For FIFO RAM mode primitive, a trailing ‘R’ or ‘W’ in the signal name specifies the FIFO read port or write port respectively.
4. For FIFO RAM mode primitive FULLI has the same function as CSW(2) and EMPTYI has the same function as CSR(2).
5. In FIFO mode, CLKW is the write port clock, CSW is the write port chip select, CLKR is the read port clock, CSR is the read port chip select, ORE is the output read enable.

Figure 2-9. Memory Core Reset

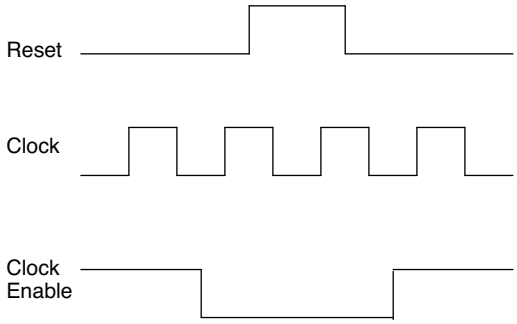


For further information on the sysMEM EBR block, please refer to TN1201, Memory Usage Guide for MachXO2 Devices.

EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the reset is released, as shown in Figure 2-10. The GSR input to the EBR is always asynchronous.

Figure 2-10. EBR Asynchronous Reset (Including GSR) Timing Diagram



If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of $1/f_{MAX}$ (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device wake up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM, ROM and FIFO implementations. For the EBR FIFO mode, the GSR signal is always enabled and the WE and RE signals act like the clock enable signals in Figure 2-10. The reset timing rules apply to the RPReset input versus the RE input and the RST input versus the WE and RE inputs. Both RST and RPReset are always asynchronous EBR inputs. For more details refer to TN1201, Memory Usage Guide for MachXO2 Devices.

Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.

DDR Memory Support

Certain PICs on the right edge of MachXO2-640U, MachXO2-1200/U and larger devices, have additional circuitry to allow the implementation of DDR memory interfaces. There are two groups of 14 or 12 PIOs each on the right edge with additional circuitry to implement DDR memory interfaces. This capability allows the implementation of up to 16-bit wide memory interfaces. One PIO from each group contains a control element, the DQS Read/Write Block, to facilitate the generation of clock and control signals (DQSR90, DQSW90, DDRCLKPOL and DATAVALID). These clock and control signals are distributed to the other PIO in the group through dedicated low skew routing.

DQS Read Write Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces a PLL is used for this adjustment. However, in DDR memories the clock (referred to as DQS) is not free-running so this approach cannot be used. The DQS Read Write block provides the required clock alignment for DDR memory interfaces. DQSR90 and DQSW90 signals are generated by the DQS Read Write block from the DQS input.

In a typical DDR memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the read cycle) is unknown. The MachXO2 family contains dedicated circuits to transfer data between these domains. To prevent set-up and hold violations, at the domain transfer between DQS (delayed) and the system clock, a clock polarity selector is used. This circuit changes the edge on which the data is registered in the synchronizing registers in the input register block. This requires evaluation at the start of each read cycle for the correct clock polarity. Prior to the read operation in DDR memories, DQS is in tri-state (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit in the DQS Read Write block detects the first DQS rising edge after the preamble state and generates the DDRCLKPOL signal. This signal is used to control the polarity of the clock to the synchronizing registers.

The temperature, voltage and process variations of the DQS delay block are compensated by a set of calibration signals (6-bit bus) from a DLL on the right edge of the device. The DLL loop is compensated for temperature, voltage and process variations by the system clock and feedback loop.

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement a wide variety of standards that are found in today's systems including LVCMOS, TTL, PCI, SSTL, HSTL, LVDS, BLVDS, MLVDS and LVPECL.

Each bank is capable of supporting multiple I/O standards. In the MachXO2 devices, single-ended output buffers, ratioed input buffers (LVTTL, LVCMOS and PCI), differential (LVDS) and referenced input buffers (SSTL and HSTL) are powered using I/O supply voltage (V_{CCIO}). Each sysIO bank has its own V_{CCIO}. In addition, each bank has a voltage reference, V_{REF}, which allows the use of referenced input buffers independent of the bank V_{CCIO}.

MachXO2-256 and MachXO2-640 devices contain single-ended ratioed input buffers and single-ended output buffers with complementary outputs on all the I/O banks. Note that the single-ended input buffers on these devices do not contain PCI clamps. In addition to the single-ended I/O buffers these two devices also have differential and referenced input buffers on all I/Os. The I/Os are arranged in pairs, the two pads in the pair are described as "T" and "C", where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

Figure 2-18. MachXO2-1200U, MachXO2-2000/U, MachXO2-4000 and MachXO2-7000 Banks

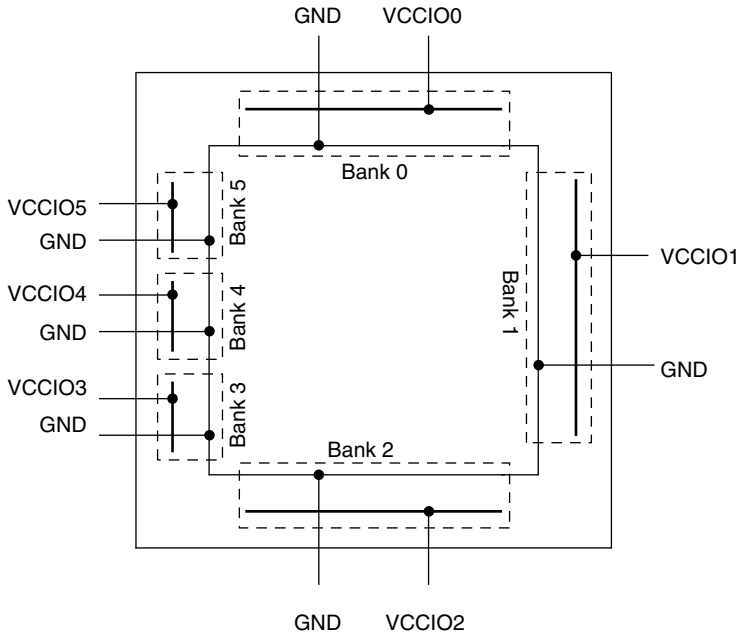
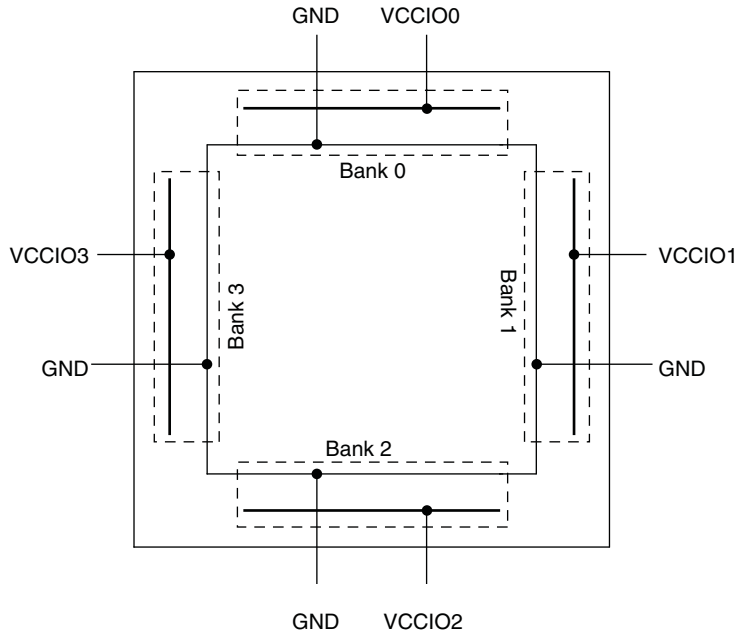


Figure 2-19. MachXO2-256, MachXO2-640/U and MachXO2-1200 Banks



There are some limitations on the use of the hardened user SPI. These are defined in the following technical notes:

- TN1087, Minimizing System Interruption During Configuration Using TransFR Technology (Appendix B)
- TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices

Figure 2-22. SPI Core Block Diagram

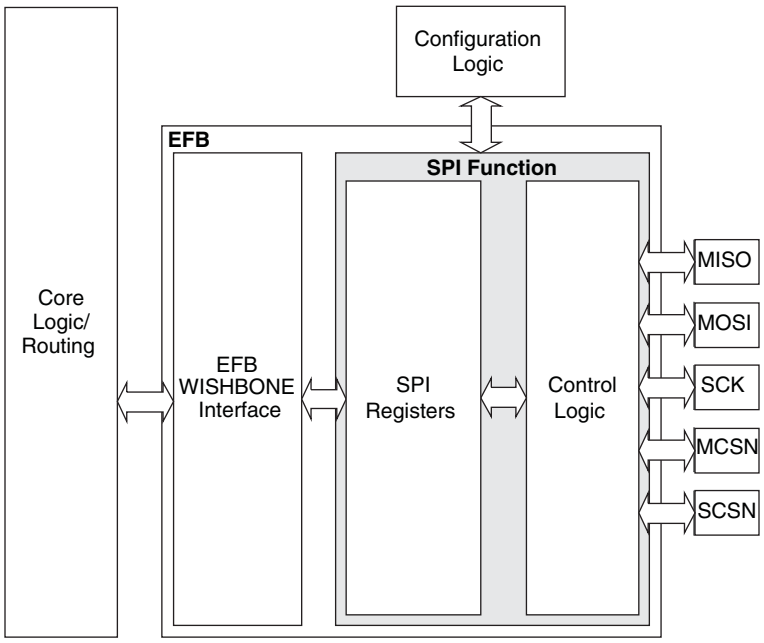


Table 2-16 describes the signals interfacing with the SPI cores.

Table 2-16. SPI Core Signal Description

Signal Name	I/O	Master/Slave	Description
spi_csn[0]	O	Master	SPI master chip-select output
spi_csn[1..7]	O	Master	Additional SPI chip-select outputs (total up to eight slaves)
spi_scsn	I	Slave	SPI slave chip-select input
spi_irq	O	Master/Slave	Interrupt request
spi_clk	I/O	Master/Slave	SPI clock. Output in master mode. Input in slave mode.
spi_miso	I/O	Master/Slave	SPI data. Input in master mode. Output in slave mode.
spi_mosi	I/O	Master/Slave	SPI data. Output in master mode. Input in slave mode.
ufm_sn	I	Slave	Configuration Slave Chip Select (active low), dedicated for selecting the User Flash Memory (UFM).
cfg_stdby	O	Master/Slave	Stand-by signal – To be connected only to the power module of the MachXO2 device. The signal is enabled only if the “Wakeup Enable” feature has been set within the EFB GUI, SPI Tab.
cfg_wake	O	Master/Slave	Wake-up signal – To be connected only to the power module of the MachXO2 device. The signal is enabled only if the “Wakeup Enable” feature has been set within the EFB GUI, SPI Tab.

Power-On-Reset Voltage Levels[1, 2, 3, 4, 5]

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for HC devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Programming/Erase Specifications

Symbol	Parameter	Min.	Max.[1]	Units
$N_{PROGCYC}$	Flash Programming cycles per $t_{RETENTION}$	—	10,000	Cycles
	Flash functional programming cycles	—	100,000	
$t_{RETENTION}$	Data retention at 100 °C junction temperature	10	—	Years
	Data retention at 85 °C junction temperature	20	—	

1. Maximum Flash memory reads are limited to 7.5E13 cycles over the lifetime of the product.

Hot Socketing Specifications[1, 2, 3]

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/–1000	µA

1. Insensitive to sequence of V_{CC} and V_{CCIO}. However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO}.
2. $0 < V_{CC} < V_{CC}$ (MAX), $0 < V_{CCIO} < V_{CCIO}$ (MAX).
3. I_{DK} is additive to I_{PU}, I_{PD} or I_{BH}.

ESD Performance

Please refer to the MachXO2 Product Family Qualification Summary for complete qualification data, including ESD performance.

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL} Max.[4] (mA)	I_{OH} Max.[4] (mA)
	Min. (V)[3]	Max. (V)	Min. (V)	Max. (V)				
LVCMOS10R25	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain

1. MachXO2 devices allow LVCMOS inputs to be placed in I/O banks where V_{CCIO} is different from what is specified in the applicable JEDEC specification. This is referred to as a ratioed input buffer. In a majority of cases this operation follows or exceeds the applicable JEDEC specification. The cases where MachXO2 devices do not meet the relevant JEDEC specification are documented in the table below.
2. MachXO2 devices allow for LVCMOS referenced I/Os which follow applicable JEDEC specifications. For more details about mixed mode operation please refer to please refer to TN1202, MachXO2 sysIO Usage Guide.
3. The dual function I^2C pins SCL and SDA are limited to a V_{IL} min of –0.25 V or to –0.3 V with a duration of <10 ns.
4. For electromigration, the average DC current sourced or sinked by I/O pads between two consecutive VCCIO or GND pad connections, or between the last VCCIO or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed a maximum of n * 8 mA. “n” is the number of I/O pads between the two consecutive bank VCCIO or GND connections or between the last VCCIO and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

Input Standard	V_{CCIO} (V)	V_{IL} Max. (V)
LVCMOS 33	1.5	0.685
LVCMOS 25	1.5	0.687
LVCMOS 18	1.5	0.655

sysIO Differential Electrical Characteristics

The LVDS differential output buffers are available on the top side of MachXO2-640U, MachXO2-1200/U and higher density devices in the MachXO2 PLD family.

LVDS

Over Recommended Operating Conditions

Parameter Symbol	Parameter Description	Test Conditions	Min.	Typ.	Max.	Units
V_{INP}, V_{INM}	Input Voltage	V_{CCIO} = 3.3 V	0	—	2.605	V
		V_{CCIO} = 2.5 V	0	—	2.05	V
V_{THD}	Differential Input Threshold		±100	—		mV
V_{CM}	Input Common Mode Voltage	V_{CCIO} = 3.3 V	0.05	—	2.6	V
		V_{CCIO} = 2.5 V	0.05	—	2.0	V
I_{IN}	Input current	Power on	—	—	±10	µA
V_{OH}	Output high voltage for V_{OP} or V_{OM}	R_T = 100 Ohm	—	1.375	—	V
V_{OL}	Output low voltage for V_{OP} or V_{OM}	R_T = 100 Ohm	0.90	1.025	—	V
V_{OD}	Output voltage differential	(V_{OP} - V_{OM}), R_T = 100 Ohm	250	350	450	mV
ΔV_{OD}	Change in V_{OD} between high and low		—	—	50	mV
V_{OS}	Output voltage offset	(V_{OP} + V_{OM})/2, R_T = 100 Ohm	1.125	1.20	1.395	V
ΔV_{OS}	Change in V_{OS} between H and L		—	—	50	mV
I_{OSD}	Output short circuit current	V_{OD} = 0 V driver outputs shorted	—	—	24	mA

BLVDS

The MachXO2 family supports the BLVDS standard through emulation. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs. The input standard is supported by the LVDS differential input buffer. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS Multi-point Output Example

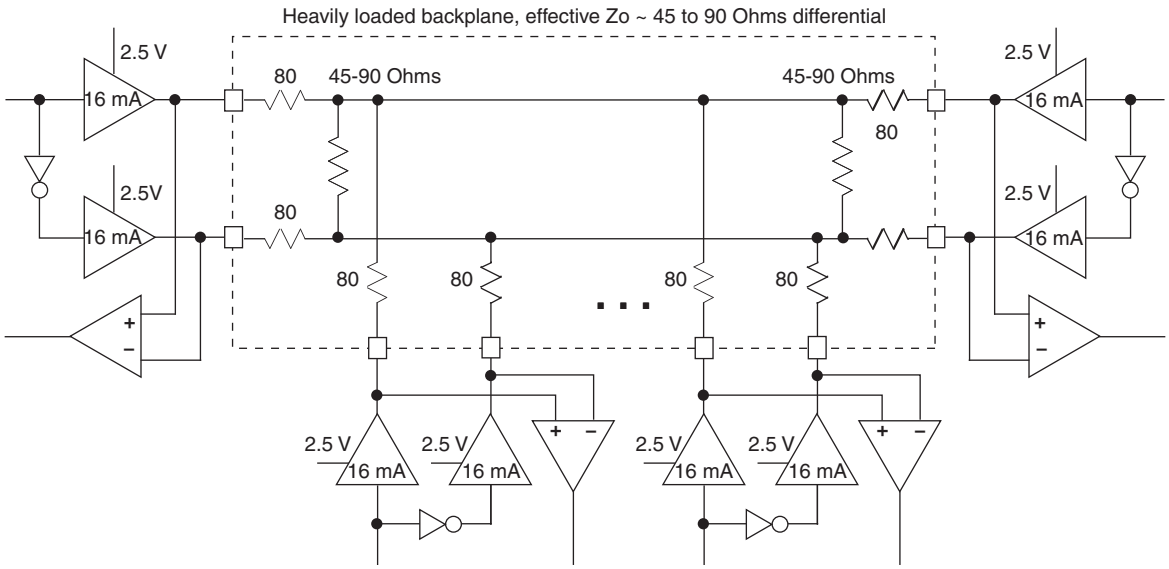


Table 3-2. BLVDS DC Conditions[1]

Over Recommended Operating Conditions

Symbol	Description	Nominal		Units
		Zo = 45	Zo = 90	
Z_{OUT}	Output impedance	20	20	Ohms
R_S	Driver series resistance	80	80	Ohms
R_{TLEFT}	Left end termination	45	90	Ohms
R_{TRIGHT}	Right end termination	45	90	Ohms
V_{OH}	Output high voltage	1.376	1.480	V
V_{OL}	Output low voltage	1.124	1.020	V
V_{OD}	Output differential voltage	0.253	0.459	V
V_{CM}	Output common mode voltage	1.250	1.250	V
I_{DC}	DC output current	11.236	10.204	mA

1. For input buffer, see LVDS table.

Typical Building Block Function Performance – HC/HE Devices[1]

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)

Function	-6 Timing	Units
Basic Functions		
16-bit decoder	8.9	ns
4:1 MUX	7.5	ns
16:1 MUX	8.3	ns

Register-to-Register Performance

Function	-6 Timing	Units
Basic Functions		
16:1 MUX	412	MHz
16-bit adder	297	MHz
16-bit counter	324	MHz
64-bit counter	161	MHz
Embedded Memory Functions		
1024x9 True-Dual Port RAM (Write Through or Normal, EBR output registers)	183	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (one PFU)	500	MHz

1. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.

MachXO2 External Switching Characteristics – HC/HE Devices[1, 2, 3, 4, 5, 6, 7]

Over Recommended Operating Conditions

Parameter	Description	Device	–6		–5		–4		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Clocks									
Primary Clocks									
f_{MAX_PRI}[8]	Frequency for Primary Clock Tree	All MachXO2 devices	—	388	—	323	—	269	MHz
t_{W_PRI}	Clock Pulse Width for Primary Clock	All MachXO2 devices	0.5	—	0.6	—	0.7	—	ns
t_{SKEW_PRI}	Primary Clock Skew Within a Device	MachXO2-256HC-HE	—	912	—	939	—	975	ps
		MachXO2-640HC-HE	—	844	—	871	—	908	ps
		MachXO2-1200HC-HE	—	868	—	902	—	951	ps
		MachXO2-2000HC-HE	—	867	—	897	—	941	ps
		MachXO2-4000HC-HE	—	865	—	892	—	931	ps
		MachXO2-7000HC-HE	—	902	—	942	—	989	ps
Edge Clock									
f_{MAX_EDGE}[8]	Frequency for Edge Clock	MachXO2-1200 and larger devices	—	400	—	333	—	278	MHz
Pin-LUT-Pin Propagation Delay									
t_{PD}	Best case propagation delay through one LUT-4	All MachXO2 devices	—	6.72	—	6.96	—	7.24	ns
General I/O Pin Parameters (Using Primary Clock without PLL)									
t_{CO}	Clock to Output – PIO Output Register	MachXO2-256HC-HE	—	7.13	—	7.30	—	7.57	ns
		MachXO2-640HC-HE	—	7.15	—	7.30	—	7.57	ns
		MachXO2-1200HC-HE	—	7.44	—	7.64	—	7.94	ns
		MachXO2-2000HC-HE	—	7.46	—	7.66	—	7.96	ns
		MachXO2-4000HC-HE	—	7.51	—	7.71	—	8.01	ns
		MachXO2-7000HC-HE	—	7.54	—	7.75	—	8.06	ns
t_{SU}	Clock to Data Setup – PIO Input Register	MachXO2-256HC-HE	–0.06	—	–0.06	—	–0.06	—	ns
		MachXO2-640HC-HE	–0.06	—	–0.06	—	–0.06	—	ns
		MachXO2-1200HC-HE	–0.17	—	–0.17	—	–0.17	—	ns
		MachXO2-2000HC-HE	–0.20	—	–0.20	—	–0.20	—	ns
		MachXO2-4000HC-HE	–0.23	—	–0.23	—	–0.23	—	ns
		MachXO2-7000HC-HE	–0.23	—	–0.23	—	–0.23	—	ns
t_{H}	Clock to Data Hold – PIO Input Register	MachXO2-256HC-HE	1.75	—	1.95	—	2.16	—	ns
		MachXO2-640HC-HE	1.75	—	1.95	—	2.16	—	ns
		MachXO2-1200HC-HE	1.88	—	2.12	—	2.36	—	ns
		MachXO2-2000HC-HE	1.89	—	2.13	—	2.37	—	ns
		MachXO2-4000HC-HE	1.94	—	2.18	—	2.43	—	ns
		MachXO2-7000HC-HE	1.98	—	2.23	—	2.49	—	ns

Parameter	Description	Device	–3		–2		–1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDR4 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Centered[9, 12]									
t_{SU}	Input Data Setup Before ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	0.434	—	0.535	—	0.630	—	ns
t_{HO}	Input Data Hold After ECLK		0.385	—	0.395	—	0.463	—	ns
f_{DATA}	DDRX4 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	210	—	176	—	146	MHz
f_{SCLK}	SCLK Frequency		—	53	—	44	—	37	MHz
7:1 LVDS Inputs – GDDR71_RX.ECLK.7.1[9, 12]									
t_{DVA}	Input Data Valid After ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	—	0.307	—	0.316	—	0.326	UI
t_{DVE}	Input Data Hold After ECLK		0.662	—	0.650	—	0.649	—	UI
f_{DATA}	DDR71 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f_{DDR71}	DDR71 ECLK Frequency		—	210	—	176	—	146	MHz
f_{CLKIN}	7:1 Input Clock Frequency (SCLK) (minimum limited by PLL)		—	60	—	50	—	42	MHz
Generic DDR Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	All MachXO2 devices, all sides	—	0.850	—	0.910	—	0.970	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.850	—	0.910	—	0.970	ns
f_{DATA}	DDRX1 Output Data Speed		—	140	—	116	—	98	Mbps
f_{DDRX1}	DDRX1 SCLK frequency		—	70	—	58	—	49	MHz
Generic DDR Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Centered[9, 12]									
t_{DVB}	Output Data Valid Before CLK Output	All MachXO2 devices, all sides	2.720	—	3.380	—	4.140	—	ns
t_{DVA}	Output Data Valid After CLK Output		2.720	—	3.380	—	4.140	—	ns
f_{DATA}	DDRX1 Output Data Speed		—	140	—	116	—	98	Mbps
f_{DDRX1}	DDRX1 SCLK Frequency (minimum limited by PLL)		—	70	—	58	—	49	MHz
Generic DDRX2 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX2_TX.ECLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only	—	0.270	—	0.300	—	0.330	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.270	—	0.300	—	0.330	ns
f_{DATA}	DDRX2 Serial Output Data Speed		—	280	—	234	—	194	Mbps
f_{DDRX2}	DDRX2 ECLK frequency		—	140	—	117	—	97	MHz
f_{SCLK}	SCLK Frequency		—	70	—	59	—	49	MHz

Parameter	Description	Device	–3		–2		–1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
LPDDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.349	—	0.381	—	0.396	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.665	—	0.630	—	0.613	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM LPDDR Serial Data Speed		—	120	—	110	—	96	Mbps
f_{SCLK}	SCLK Frequency		—	60	—	55	—	48	MHz
f_{LPDDR}	LPDDR Data Transfer Rate		0	120	0	110	0	96	Mbps
DDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.347	—	0.374	—	0.393	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.665	—	0.637	—	0.616	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	140	—	116	—	98	Mbps
f_{SCLK}	SCLK Frequency		—	70	—	58	—	49	MHz
f_{MEM_DDR}	MEM DDR Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps
DDR2[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.372	—	0.394	—	0.410	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.690	—	0.658	—	0.618	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	140	—	116	—	98	Mbps
f_{SCLK}	SCLK Frequency		—	70	—	58	—	49	MHz
f_{MEM_DDR2}	MEM DDR2 Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0 pf load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.
5. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
6. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03\ ns)/2$.
7. The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 167 ps (–3), 182 ps (–2), 195 ps (–1).
8. This number for general purpose usage. Duty cycle tolerance is +/–10%.
9. Duty cycle is +/– 5% for system usage.
10. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
11. High-speed DDR and LVDS not supported in SG32 (32-Pin QFN) packages.
12. Advance information for MachXO2 devices in 48 QFN packages.
13. DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.

sysCLOCK PLL Timing (Continued)

Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Min.	Max.	Units
t_{ROTATE_WD}	PHASESTEP Pulse Width		4	—	VCO Cycles

1. Period jitter sample is taken over 10,000 samples of the primary PLL output with a clean reference clock. Cycle-to-cycle jitter is taken over 1000 cycles. Phase jitter is taken over 2000 cycles. All values per JESD65B.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Using LVDS output buffers.
4. CLKOS as compared to CLKOP output for one phase step at the maximum VCO frequency. See TN1199, MachXO2 sysCLOCK PLL Design and Usage Guide for more details.
5. At minimum $f_{PFD.}$ As the f_{PFD} increases the time will decrease to approximately 60% the value listed.
6. Maximum allowed jitter on an input clock. PLL unlock may occur if the input jitter exceeds this specification. Jitter on the input clock may be transferred to the output clocks, resulting in jitter measurements outside the output specifications listed in this table.
7. Edge Duty Trim Accuracy is a percentage of the setting value. Settings available are 70 ps, 140 ps, and 280 ps in addition to the default value of none.
8. Jitter values measured with the internal oscillator operating. The jitter values will increase with loading of the PLD fabric and in the presence of SSO noise.

Pinout Information Summary

	MachXO2-256					MachXO2-640			MachXO2-640U
	32 QFN[1]	48 QFN[3]	64 ucBGA	100 TQFP	132 csBGA	48 QFN[3]	100 TQFP	132 csBGA	144 TQFP
General Purpose I/O per Bank									
Bank 0	8	10	9	13	13	10	18	19	27
Bank 1	2	10	12	14	14	10	20	20	26
Bank 2	9	10	11	14	14	10	20	20	28
Bank 3	2	10	12	14	14	10	20	20	26
Bank 4	0	0	0	0	0	0	0	0	0
Bank 5	0	0	0	0	0	0	0	0	0
Total General Purpose Single Ended I/O	21	40	44	55	55	40	78	79	107
Differential I/O per Bank									
Bank 0	4	5	5	7	7	5	9	10	14
Bank 1	1	5	6	7	7	5	10	10	13
Bank 2	4	5	5	7	7	5	10	10	14
Bank 3	1	5	6	7	7	5	10	10	13
Bank 4	0	0	0	0	0	0	0	0	0
Bank 5	0	0	0	0	0	0	0	0	0
Total General Purpose Differential I/O	10	20	22	28	28	20	39	40	54
Dual Function I/O	22	25	27	29	29	25	29	29	33
High-speed Differential I/O									
Bank 0	0	0	0	0	0	0	0	0	7
Gearboxes									
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	0	0	0	0	0	0	0	0	7
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	0	0	0	0	0	0	0	0	7
DQS Groups									
Bank 1	0	0	0	0	0	0	0	0	2
VCCIO Pins									
Bank 0	2	2	2	2	2	2	2	2	3
Bank 1	1	1	2	2	2	1	2	2	3
Bank 2	2	2	2	2	2	2	2	2	3
Bank 3	1	1	2	2	2	1	2	2	3
Bank 4	0	0	0	0	0	0	0	0	0
Bank 5	0	0	0	0	0	0	0	0	0
VCC	2	2	2	2	2	2	2	2	4
GND[2]	2	1	8	8	8	1	8	10	12
NC	0	0	1	26	58	0	3	32	8
Reserved for Configuration	1	1	1	1	1	1	1	1	1
Total Count of Bonded Pins	32	49	64	100	132	49	100	132	144

1. Lattice recommends soldering the central thermal pad onto the top PCB ground for improved thermal resistance.
2. For 48 QFN package, exposed die pad is the device ground.
3. 48-pin QFN information is 'Advanced'.

For Further Information

For further information regarding logic signal connections for various packages please refer to the MachXO2 Device Pinout Files.

Thermal Management

Thermal management is recommended as part of any sound FPGA design methodology. To assess the thermal characteristics of a system, Lattice specifies a maximum allowable junction temperature in all device data sheets. Users must complete a thermal analysis of their specific design to ensure that the device and package do not exceed the junction temperature limits. Refer to the Thermal Management document to find the device/package specific thermal values.

For Further Information

For further information regarding Thermal Management, refer to the following:

- Thermal Management document
- TN1198, Power Estimation and Management for MachXO2 Devices
- The Power Calculator tool is included with the Lattice design tools, or as a standalone download from www.latticesemi.com/software

High-Performance Commercial Grade Devices without Voltage Regulator, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000HE-4TG100C	2112	1.2 V	–4	Halogen-Free TQFP	100	COM
LCMXO2-2000HE-5TG100C	2112	1.2 V	–5	Halogen-Free TQFP	100	COM
LCMXO2-2000HE-6TG100C	2112	1.2 V	–6	Halogen-Free TQFP	100	COM
LCMXO2-2000HE-4TG144C	2112	1.2 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-2000HE-5TG144C	2112	1.2 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-2000HE-6TG144C	2112	1.2 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-2000HE-4MG132C	2112	1.2 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-2000HE-5MG132C	2112	1.2 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-2000HE-6MG132C	2112	1.2 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-2000HE-4BG256C	2112	1.2 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-2000HE-5BG256C	2112	1.2 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-2000HE-6BG256C	2112	1.2 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-2000HE-4FTG256C	2112	1.2 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-2000HE-5FTG256C	2112	1.2 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-2000HE-6FTG256C	2112	1.2 V	–6	Halogen-Free ftBGA	256	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHE-4FG484C	2112	1.2 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHE-5FG484C	2112	1.2 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHE-6FG484C	2112	1.2 V	–6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HE-4TG144C	4320	1.2 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-4000HE-5TG144C	4320	1.2 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-4000HE-6TG144C	4320	1.2 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-4000HE-4MG132C	4320	1.2 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-4000HE-5MG132C	4320	1.2 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-4000HE-6MG132C	4320	1.2 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-4000HE-4BG256C	4320	1.2 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-4000HE-4MG184C	4320	1.2 V	–4	Halogen-Free csBGA	184	COM
LCMXO2-4000HE-5MG184C	4320	1.2 V	–5	Halogen-Free csBGA	184	COM
LCMXO2-4000HE-6MG184C	4320	1.2 V	–6	Halogen-Free csBGA	184	COM
LCMXO2-4000HE-5BG256C	4320	1.2 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-4000HE-6BG256C	4320	1.2 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-4000HE-4FTG256C	4320	1.2 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-4000HE-5FTG256C	4320	1.2 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-4000HE-6FTG256C	4320	1.2 V	–6	Halogen-Free ftBGA	256	COM
LCMXO2-4000HE-4BG332C	4320	1.2 V	–4	Halogen-Free caBGA	332	COM
LCMXO2-4000HE-5BG332C	4320	1.2 V	–5	Halogen-Free caBGA	332	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1TG100IR1[1]	1280	1.2 V	–1	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-2TG100IR1[1]	1280	1.2 V	–2	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-3TG100IR1[1]	1280	1.2 V	–3	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-1MG132IR1[1]	1280	1.2 V	–1	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-2MG132IR1[1]	1280	1.2 V	–2	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-3MG132IR1[1]	1280	1.2 V	–3	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-1TG144IR1[1]	1280	1.2 V	–1	Halogen-Free TQFP	144	IND
LCMXO2-1200ZE-2TG144IR1[1]	1280	1.2 V	–2	Halogen-Free TQFP	144	IND
LCMXO2-1200ZE-3TG144IR1[1]	1280	1.2 V	–3	Halogen-Free TQFP	144	IND

1. Specifications for the “LCMXO2-1200ZE-speed package IR1” are the same as the “LCMXO2-1200ZE-speed package I” devices respectively, except as specified in the R1 Device Specifications section of this data sheet.

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200HC-4SG32I	1280	2.5 V / 3.3 V	–4	Halogen-Free QFN	32	IND
LCMXO2-1200HC-5SG32I	1280	2.5 V / 3.3 V	–5	Halogen-Free QFN	32	IND
LCMXO2-1200HC-6SG32I	1280	2.5 V / 3.3 V	–6	Halogen-Free QFN	32	IND
LCMXO2-1200HC-4TG100I	1280	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	IND
LCMXO2-1200HC-5TG100I	1280	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	IND
LCMXO2-1200HC-6TG100I	1280	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	IND
LCMXO2-1200HC-4MG132I	1280	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	IND
LCMXO2-1200HC-5MG132I	1280	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	IND
LCMXO2-1200HC-6MG132I	1280	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	IND
LCMXO2-1200HC-4TG144I	1280	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-1200HC-5TG144I	1280	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-1200HC-6TG144I	1280	2.5 V/ 3.3 V	–6	Halogen-Free TQFP	144	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200UHC-4FTG256I	1280	2.5 V / 3.3 V	–4	Halogen-Free ftBGA	256	IND
LCMXO2-1200UHC-5FTG256I	1280	2.5 V / 3.3 V	–5	Halogen-Free ftBGA	256	IND
LCMXO2-1200UHC-6FTG256I	1280	2.5 V / 3.3 V	–6	Halogen-Free ftBGA	256	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000HC-4TG100I	2112	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	IND
LCMXO2-2000HC-5TG100I	2112	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	IND
LCMXO2-2000HC-6TG100I	2112	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	IND
LCMXO2-2000HC-4MG132I	2112	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	IND
LCMXO2-2000HC-5MG132I	2112	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	IND
LCMXO2-2000HC-6MG132I	2112	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	IND
LCMXO2-2000HC-4TG144I	2112	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-2000HC-5TG144I	2112	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-2000HC-6TG144I	2112	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	IND
LCMXO2-2000HC-4BG256I	2112	2.5 V / 3.3 V	–4	Halogen-Free caBGA	256	IND
LCMXO2-2000HC-5BG256I	2112	2.5 V / 3.3 V	–5	Halogen-Free caBGA	256	IND
LCMXO2-2000HC-6BG256I	2112	2.5 V / 3.3 V	–6	Halogen-Free caBGA	256	IND
LCMXO2-2000HC-4FTG256I	2112	2.5 V / 3.3 V	–4	Halogen-Free ftBGA	256	IND
LCMXO2-2000HC-5FTG256I	2112	2.5 V / 3.3 V	–5	Halogen-Free ftBGA	256	IND
LCMXO2-2000HC-6FTG256I	2112	2.5 V / 3.3 V	–6	Halogen-Free ftBGA	256	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHC-4FG484I	2112	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	484	IND
LCMXO2-2000UHC-5FG484I	2112	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	484	IND
LCMXO2-2000UHC-6FG484I	2112	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	484	IND